



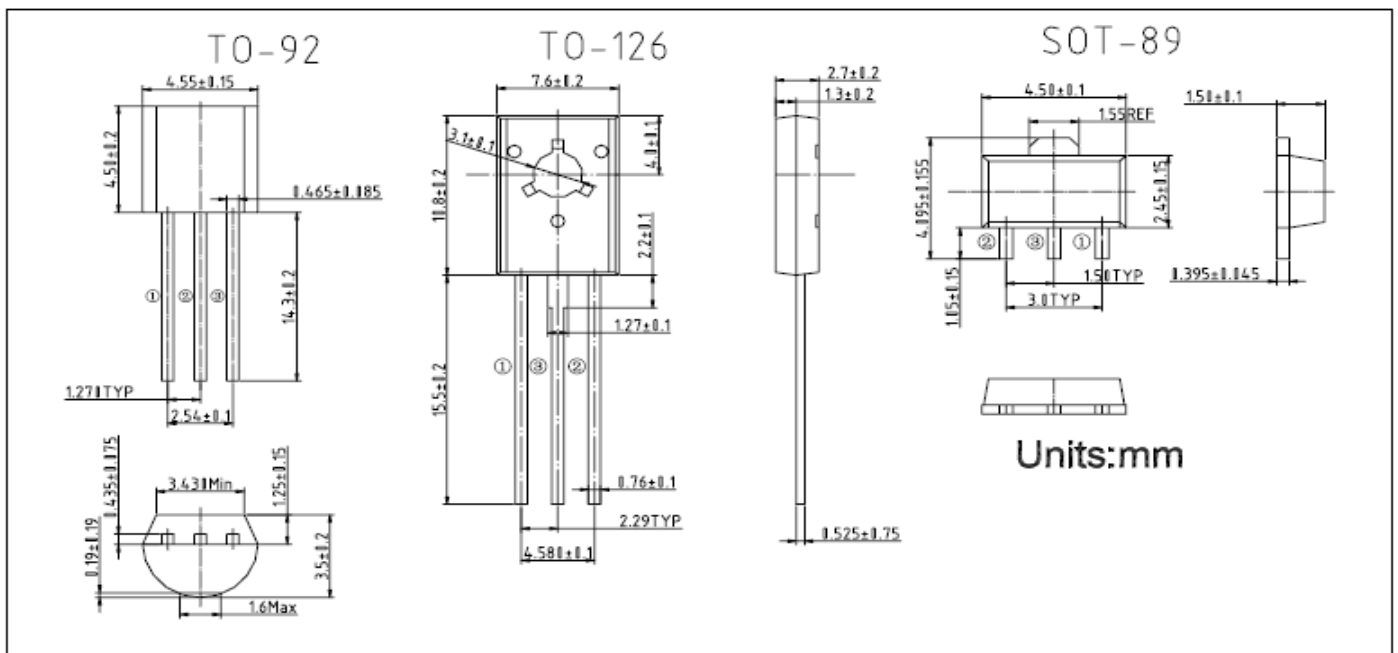
TRANSISTOR (PNP)

Plastic-Encapsulate Transistors(-40V,-3A)

● **Features**

High current output up to 3A
Low saturation Voltage

● **Package Information**



● **Pin Configuration**

	TO-92	TO126	SOT89
1	E	E	E
2	C	C	B
3	B	B	C

● **Classification of $H_{FE(1)}$**

Rank	Range
R	60-120
Q	100-200
P	160-320
E	200-400

● **ABSOLUTE Maximum Ratings (Ta=25°C Unless otherwise noted)**

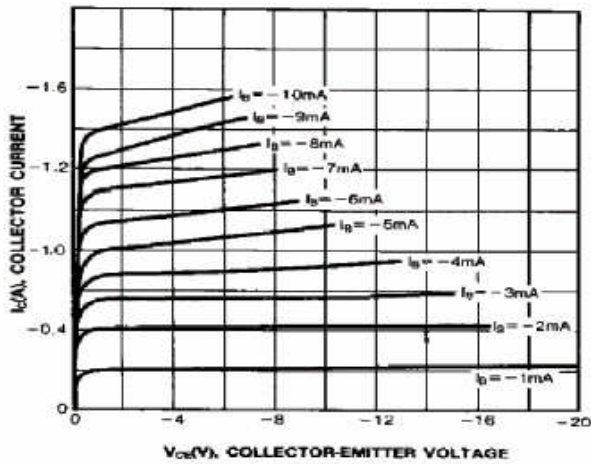
Parameter	Symbol	Value	Units
Power dissipation	P_{CM}	TO-92	0.75
		SOT-89	1.0
		TO-126	1.25
Collector current	I_{CM}	-3	A
Collector-base voltage	$V_{(BR)CBO}$	-40	V
junction temperature	T_J	-55 to 150	°C
Storage range	T_{stg}	-55 to 150	°C

● **Electrical Characteristics** ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Collector-base breakdown voltage	$V(BR)_{CBO}$	$I_C = -100\mu A, I_E = 0$	-40	--	--	V
Collector-emitter breakdown voltage	$V(BR)_{CEO}$	$I_C = -10 mA, I_B = 0$	-30	--	--	V
Emitter-base breakdown voltage	$V(BR)_{EBO}$	$I_E = -100\mu A, I_C = 0$	-5	--	--	V
Collector cut-off current	I_{CBO}	$V_{CB} = -40 V, I_E = 0$	--	--	-1	μA
Collector cut-off current	I_{CEO}	$V_{CE} = -30 V, I_B = 0$	--	--	-1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -6 V, I_C = 0$	--	--	-1	μA
DC current gain	$H_{FE(1)}$	$V_{CE} = -2 V, I_C = -1 A$	60	--	400	
	$H_{FE(2)}$	$V_{CE} = -2 V, I_C = -100 mA$	32	--	--	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -2 A, I_B = -0.2 A$	--	--	-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -2 A, I_B = -0.2 A$	--	--	-2	V
Transition frequency	f_T	$V_{CE} = -5 V, I_C = -0.1 A$ $f = 10 MHz$	50	--	--	MHz

● **Typical Performance Characteristics**

STATIC CHARACTERISTIC



DC CURRENT GAIN

